



# On Analog Power Consumption

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## **Outline**

**Introduction**

**Basics of analog power consumption**

**Comparison to digital**

**Further work**

**Application: ADC**

**Conclusions**

# Introduction

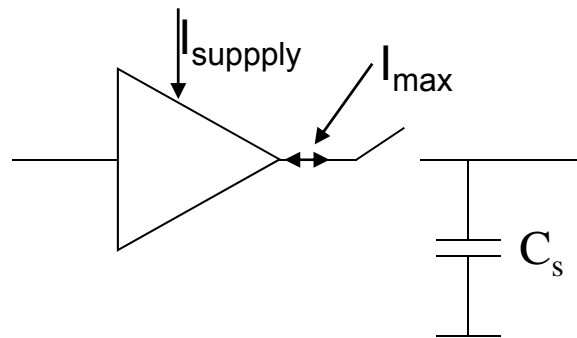
**Analog power consumption is complex and badly understood**

**Text books and practice specialize on performance constraints rather than power**

**This is an attempt to address analog design for low power and to define lower bounds to analog power consumption**

# Basics of analog power consumption

## Ideal sampler



Noise voltage generated:  $v_{nS}^2 = \frac{kT}{C_s}$

Maximum sine voltage with supply voltage  $V_{FS}$ :

$v_s^2 = \frac{V_{FS}^2}{8}$  Gives dynamic range:  $DR = \frac{v_s^2}{v_{nS}^2} = \frac{V_{FS}^2 C_s}{8kT}$

or, capacitance needed:  $C_s = \frac{8kTDR}{V_{FS}^2}$

To drive the capacitor we need a current of  $I = C_s V_{FS} 2f_s$ ,

leading to a power consumption of  $P_S = IV_{FS} = 16kTf_s DR$

# Basics of analog power consumption

## Ideal sampler

$$P_S = IV_{FS} = 16kTf_s DR$$

This expression is valid for any switched capacitor circuit  
(Example a first order switched capacitor filter)  
First described by Vittoz 1990.

Note that this expression is *independent of technology*

Note that this expression is *independent of supply voltage*  
(but assumed  $V_{FS}=V_{dd}$ ;  $V_{dd}$  is supply voltage)

# Basics of analog power consumption

## Ideal sampler - impact of technology

In the above derivation we used  $C_S = \frac{8kTDR}{V_{FS}^2}$

But  $C_S$  can not be made smaller than the smallest capacitance of the actual technology,  $C_{min}$ .

So actually we should use  $C = \max(C_S, C_{min})$  in power estimation.

In the following we use the input capacitance of a minimum inverter as  $C_{min}$ .  $C_{min} = 4 * C_{gn}$ .  $C_{gn}$  will scale with technology as the feature size (half feature size - half capacitance)

# Basics of analog power consumption

## Ideal sampler - impact of technology

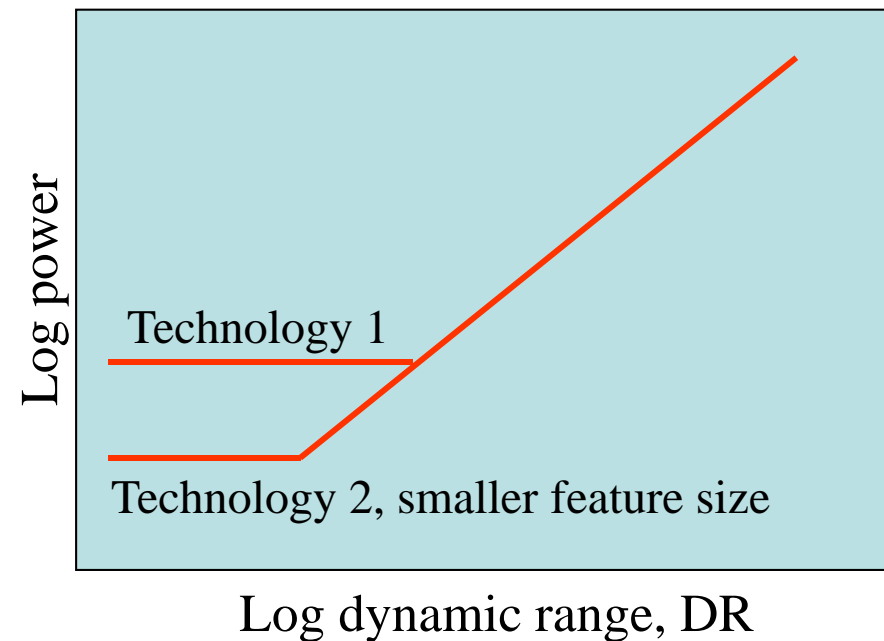
Large DR - independent technology

Smaller DR - technology dependent

Smaller feature size - less power

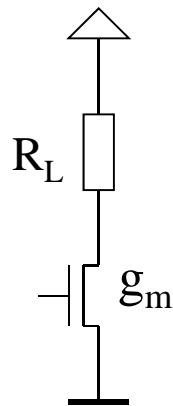
Note, scaled as (feature size)<sup>3</sup>

$$(P_S \sim V_{FS}^2 C_{min})$$



# Basics of analog power consumption

## The transistor



Drain noise current:  $i_{nD}^2 = 4kT\gamma g_m B$

Equivalent input noise:  $v_{nG}^2 = 4kT\gamma \frac{1}{g_m} B$

Dynamic range:  $DR = \frac{V_{FS}^2}{8} \frac{g_m}{4kT\gamma B}$

Required  $g_m$  for dynamic range DR:  $g_m = \frac{32kT\gamma B}{V_{FS}^2} DR$

Required drain current:  $I_D = g_m V_{eff}$

Power consumption:  $P = IV_{FS} = 32kT\gamma B \frac{V_{eff}}{V_{FS}} DR$  (compare  $P_S = 16kTf_s DR$ )



# Basics of analog power consumption

## The transistor – a note on $V_{\text{eff}}$ and $\gamma$

$V_{\text{eff}}$  definition:  $V_{\text{eff}} = I_D / g_m$        $\gamma$  defined from noise measurements

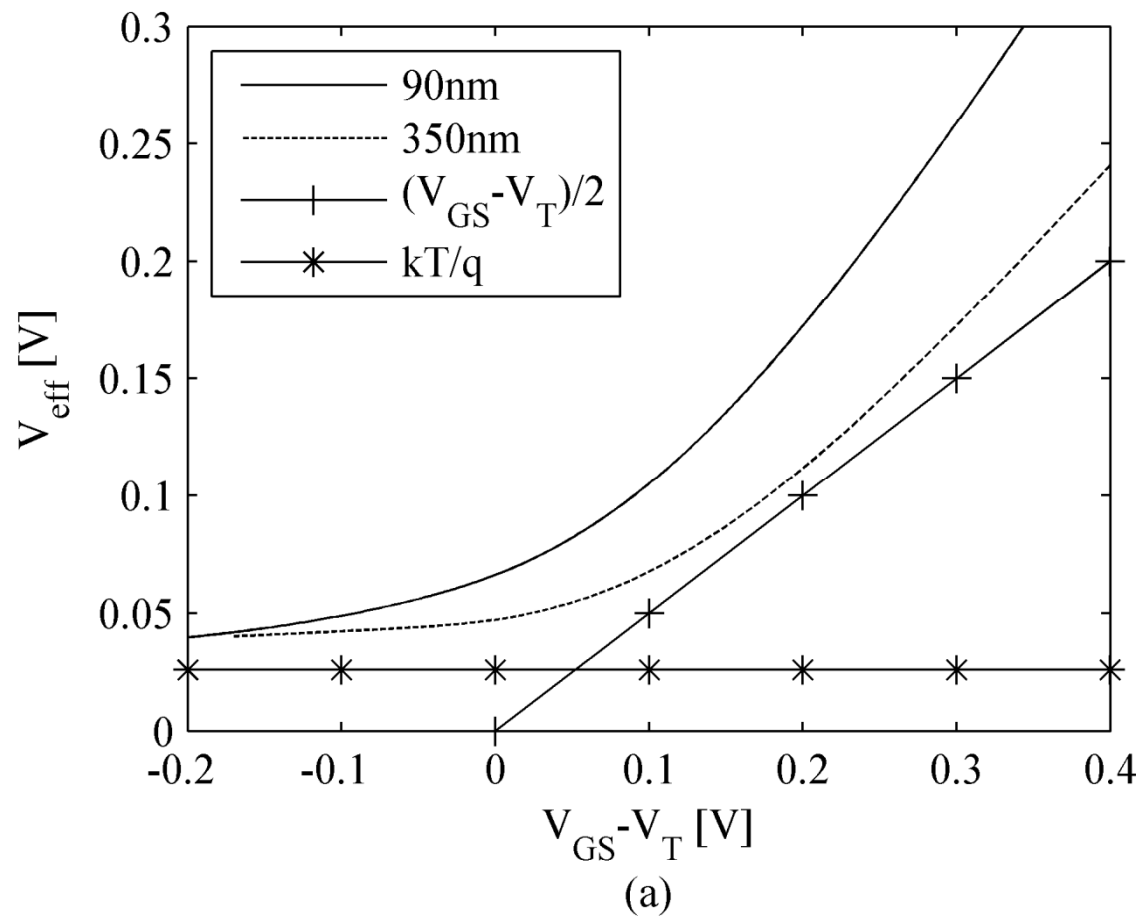
Bipolar transistor:  $V_{\text{eff}} = kT/q$        $\gamma = 1/2$  (shot noise)

Long channel MOST:  $V_{\text{eff}} = (V_G - V_T)/2$        $\gamma = 2/3$  (resistance noise)

Long channel MOST in subthreshold:  $V_{\text{eff}} = mkT/q$ ,  $m = 1.2 \dots 1.5$

Submicron MOST:  $V_{\text{eff}}$  in transition region       $\gamma \sim 1.5 - 2$

# Basics of analog power consumption



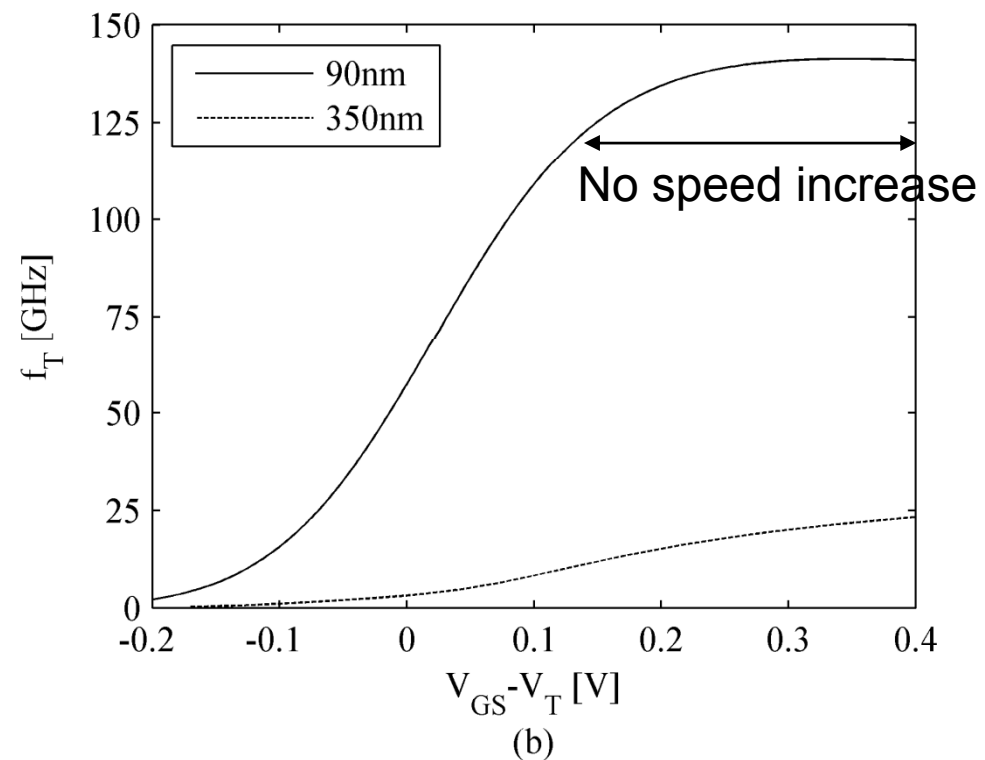
$V_{eff}$  vs  $V_G$  for  
a 90nm process  
a 350 nm process

# Basics of analog power consumption

## The transistor – a note on $V_{\text{eff}}$ and speed.

Speed controlled by  $f_T$

$$f_T = g_m / 2\pi C_g$$



# Basics of analog power consumption

## The transistor – a note on $V_{\text{eff}}$ and input swing

For a linear transistor behaviour we expect a limited drain current variation, say  $I_{\text{DC}} \pm \Delta I_{\text{d}} = I_{\text{DC}} \pm I_{\text{DC}}/2$ , with  $I_{\text{DC}} = g_{\text{m}} V_{\text{eff}}$ .

We then have  $\Delta V_{\text{g}} = \Delta i_{\text{d}} / g_{\text{m}} = V_{\text{eff}} / 2$ , or  $V_{\text{FSin}} = 2\Delta V_{\text{g}} = V_{\text{eff}}$

High linearity may require lower swing,  $V_{\text{FSin}} < V_{\text{eff}}$

# Basics of analog power consumption

## The transistor – a note on $V_{dd}$

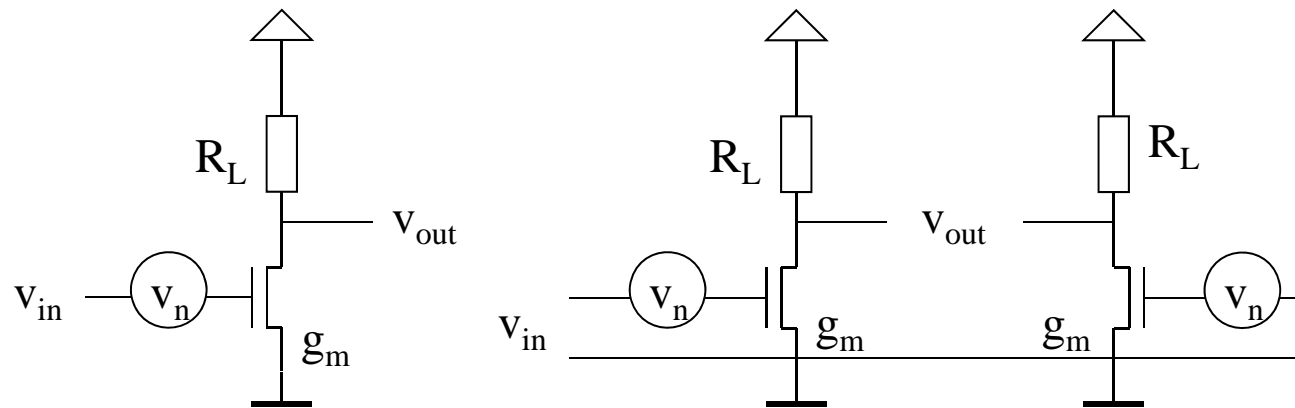
We assumed supply voltage =  $V_{FS}$

With higher supply,  $V_{dd}$ , we define voltage efficiency  $\eta_v = V_{FS}/V_{dd}$

Then power *increases* by  $1/\eta_v$

# Basics of analog power consumption

## The transistor – a note on differential circuits



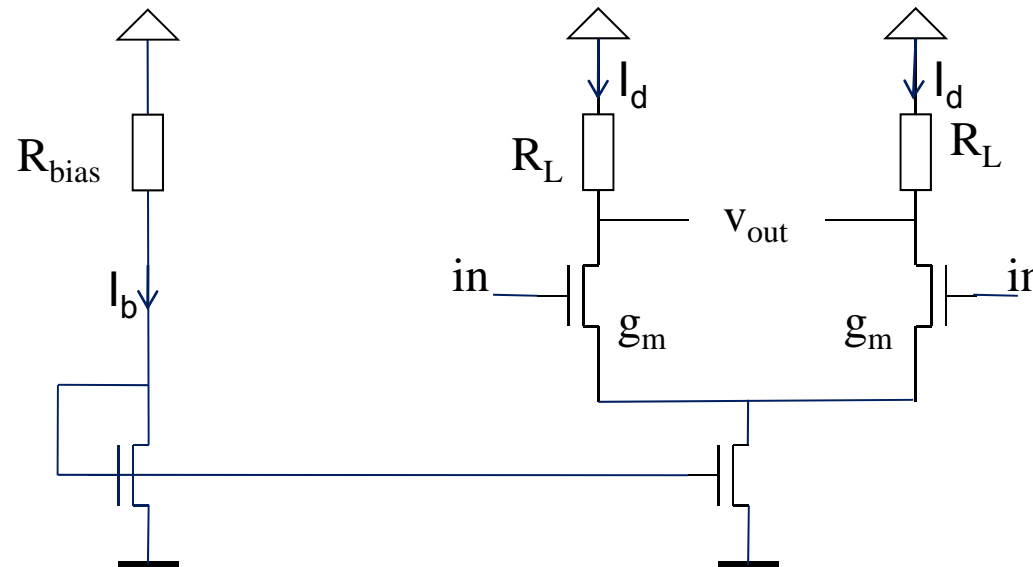
Same transistors, same bias, same signal per transistor

$$DR_{diff} = \frac{(2v_{in})^2}{2v_n^2} = 2DR_{SE} \quad P_{diff} = 2P_{SE}$$

Same dynamic range  
Same power

# Basics of analog power consumption

## The transistor – a note on bias circuits



Current efficiency,  $\eta_I = 2I_d / (I_b + 2I_d)$ . Note,  $I_b$  may need to be large for eg. low noise

Note – bias circuit may be shared

# Basics of analog power consumption

## The transistor – impact of technology

### Regarding minimum $g_m$ .

We can always reduce  $g_m$  to adapt to DR by reducing  $V_G$ .

BUT this leads to small  $V_{eff}$ , which may limit speed or input swing

Maybe we will have  $g_{mmin}$  and  $I_{DCmin}$ .

### Power proportional to $V_{eff}/V_{FS}$

Classical CMOS, this relation was kept constant

$V_{FS}$  ( $V_{dd}$ ),  $V_G$  and  $V_T$  scaled with process scaling

Submicron CMOS,  $V_{eff}$  is reduced very slowly.

*So power may increase with reduced supply voltage! (Annema et. al.)*



# Basics of analog power consumption

## The transistor – a conclusion

A transistor amplifier (single ended or differential) uses power:

$$P = IV_{FS} = 32kT\gamma B \frac{V_{eff}}{V_{FS}} DR$$

*This is constrained by:*

Increased by  $1/\eta_v$  for  $V_{FS} < V_{dd}$

Increased by  $1/\eta_i$  for extra currents (eg. bias)

$V_{eff}$  must be large enough for transistor speed ( $f_T - g_m/2\pi C_g$  large enough)

$V_{eff}$  must exceed input swing,  $V_{FSin}$ , related to linearity requirements

Technology dependence at low DR - complex

# Comparison to digital

## Comparison to analog

Consider a single pole filter / 1-tap FIR filter

Analog, use transistor formula:  
(with  $DR=3 \bullet 2^{2n}/2$ ;  $B=f_s/2$ )

$$P_a = 24kT\gamma \frac{V_{eff}}{V_{FS}} f_s 2^{2n}$$

Digital. Need 1 m-coefficient, n-bit multiplier plus 1 n-bit adder  
Multiplier uses m adders; 1 adder use n FAs (full adders); each FA  
uses equivalent 9 inverters, ie.  $C=9C_{min}$ . Totally  $9(m+1)nC_{min}$ ,  
With  $m=6$  we have  $63nC_{min}$ .

$$P_d = \frac{1}{2} \alpha f_c 63nC_{min} V_{dd}^2$$

# Comparison to digital

## Comparison to analog

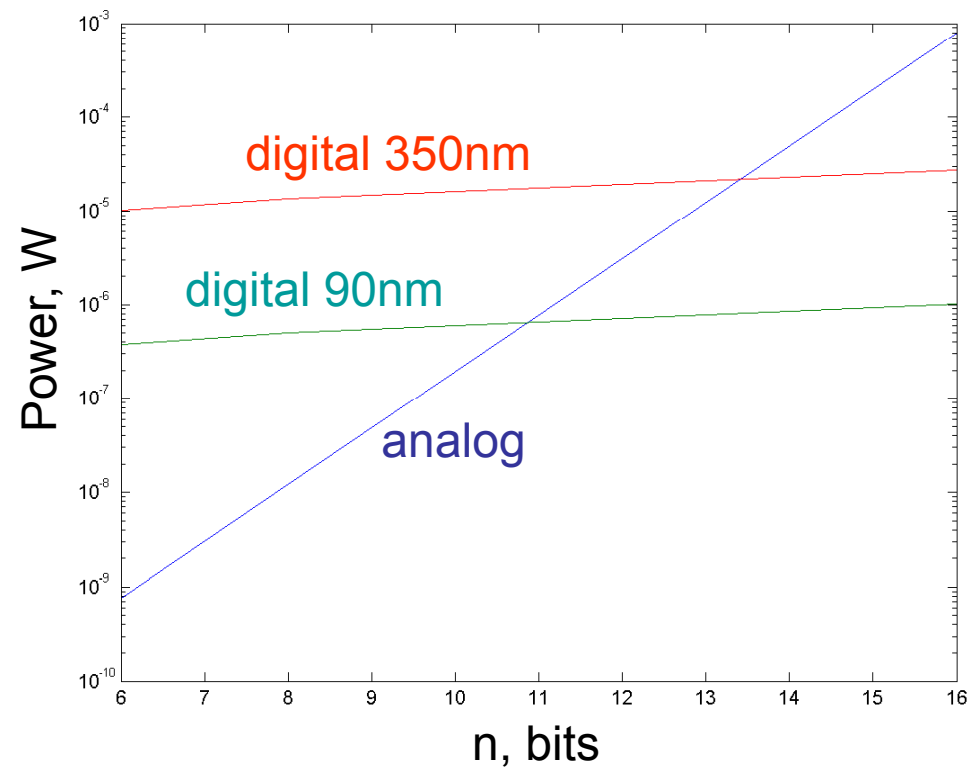
$$f_s = 20\text{MHz}$$

$$\gamma = 1.5$$

$$V_{\text{eff}} = 0.1V_{\text{FS}}$$

90nm:  $V_{\text{dd}} = 1\text{V}$   
 $C_{\text{min}} = 1\text{fF}$   
 $\alpha = 0.1$

350nm  $V_{\text{dd}} = 3\text{V}$   
 $C_{\text{min}} = 3\text{fF}$   
 $\alpha = 0.1$



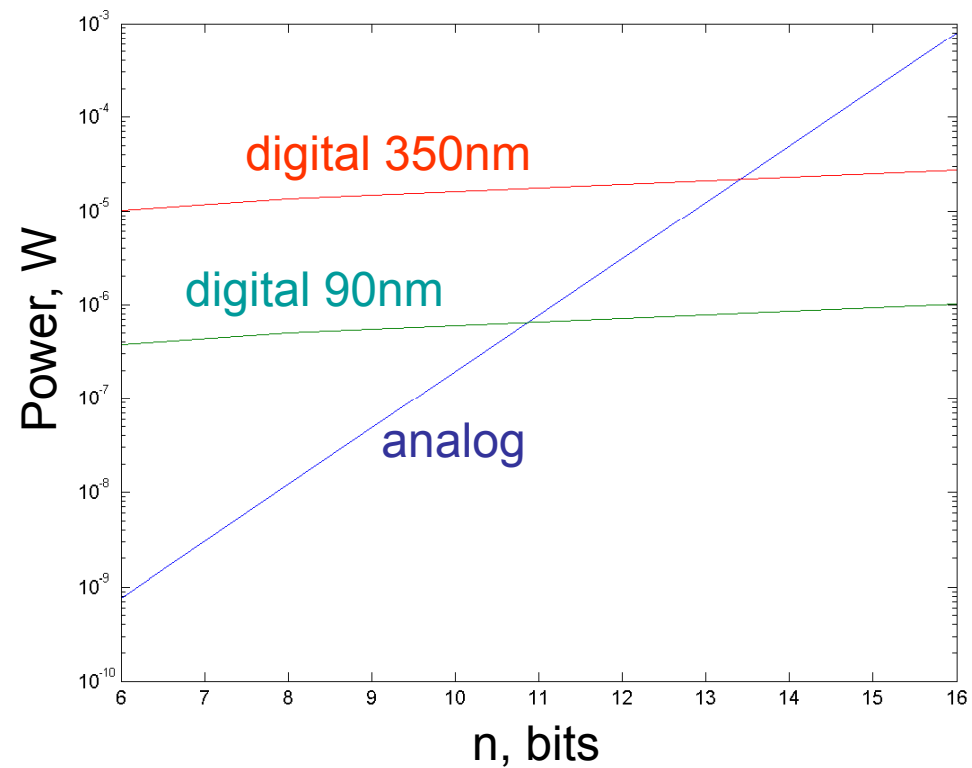
# Comparison to digital

## Comparison to analog

Analog preferred for low DR

Digital preferred for large DR

Digital improved by scaling



## Further work

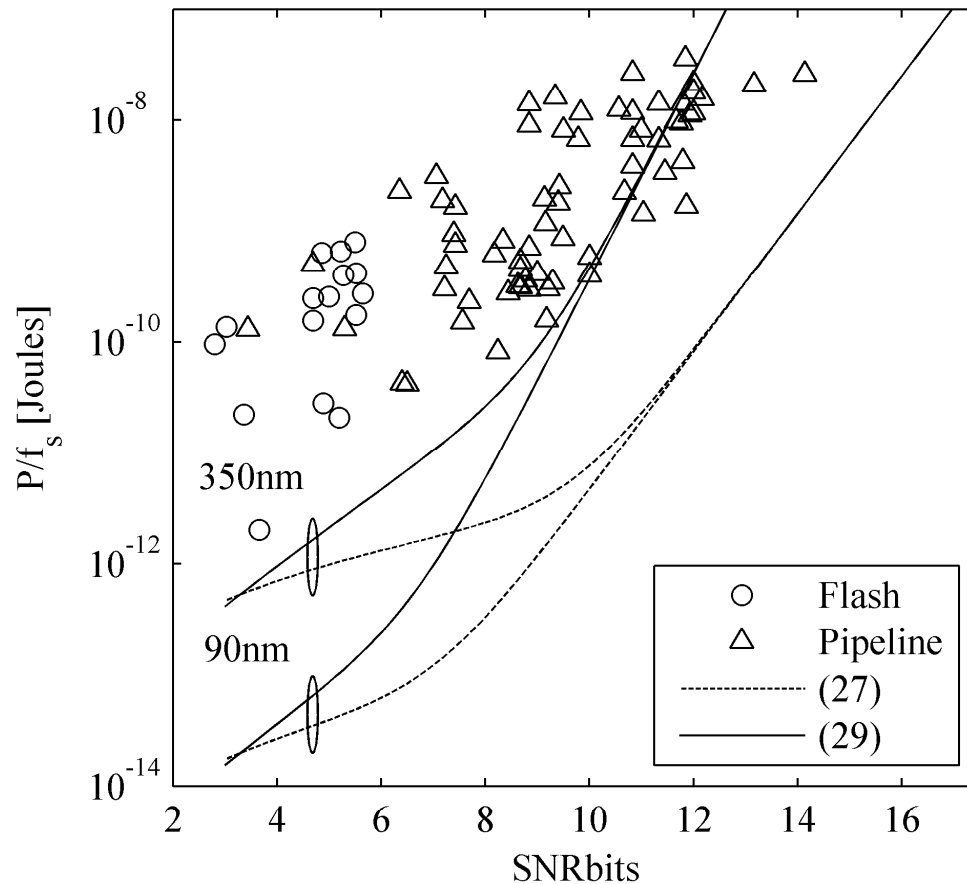
**Matching** may require large  $C$  - increased power

**Linearity** may require smaller  $V_{FS}$  – increased power

**RF circuits** can utilize passive matching – may decrease power

**Power amplifiers** need other goals – high efficiency

# Applications: ADC



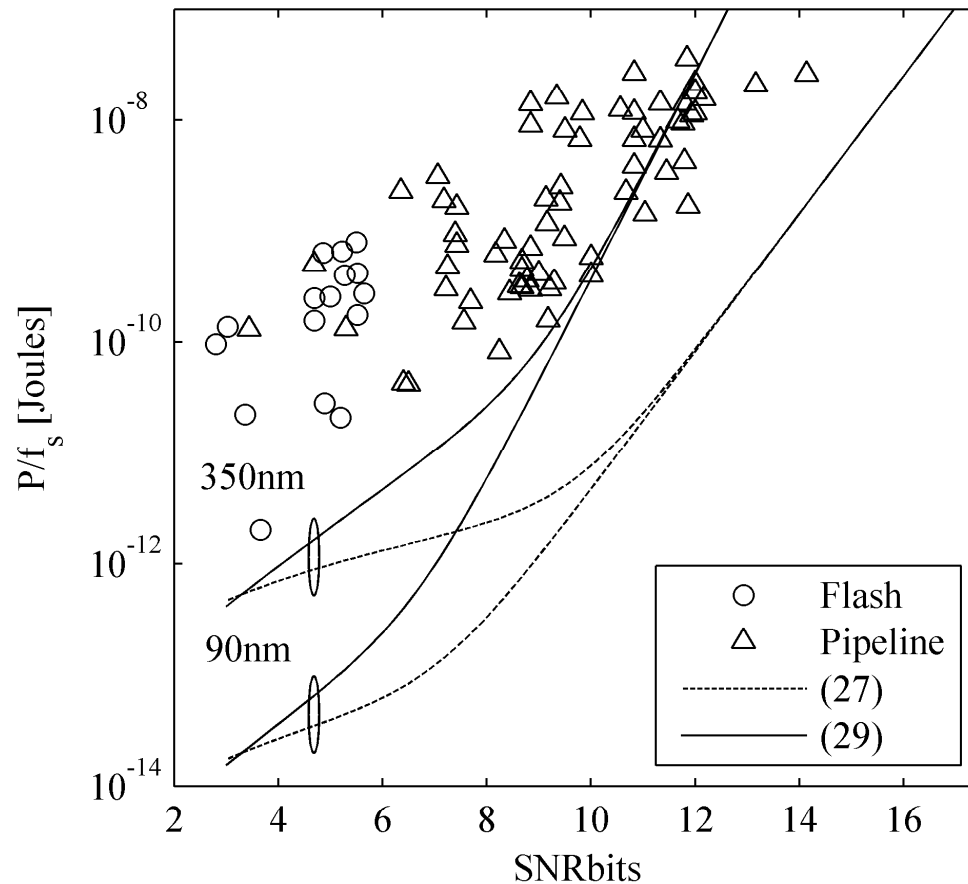
Plot of minimum ADC power for two processes

“(27)” this theory pipelined ADC  
“(29)”, theory flash ADC

Two processes, 90nm and 350nm  
( $V_{dd}=1V$ ,  $V_{eff}=100mV$ ,  $C_{min}=1fF$ ,  
 $V_{dd}=3V$ ,  $V_{eff}=300mV$ ,  $C_{min}=3fF$ )

Triangles, experimental pipelined  
Circles, experimental flash

# Applications: ADC



**Note1:**

**High resolution, noise limited**  
**Low resolution, process limited**

**Note2:**

**High resolution, experimental approaches theory (10x difference)**

**Low resolution, larger discrepancy (larger development potential)**

# Conclusions

**Power consumption in analog parts can be addressed**

**Smart choices of architecture, circuit topology, and parameters can save power**

**For large dynamic range, digital often use less power**

More so in scaled technologies

Move functions to digital

Perform digital correction of analog parts to save analog power



# References

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